

## Supporting Information for Solution-grown aligned C<sub>60</sub> single-crystals for field-effect transistors

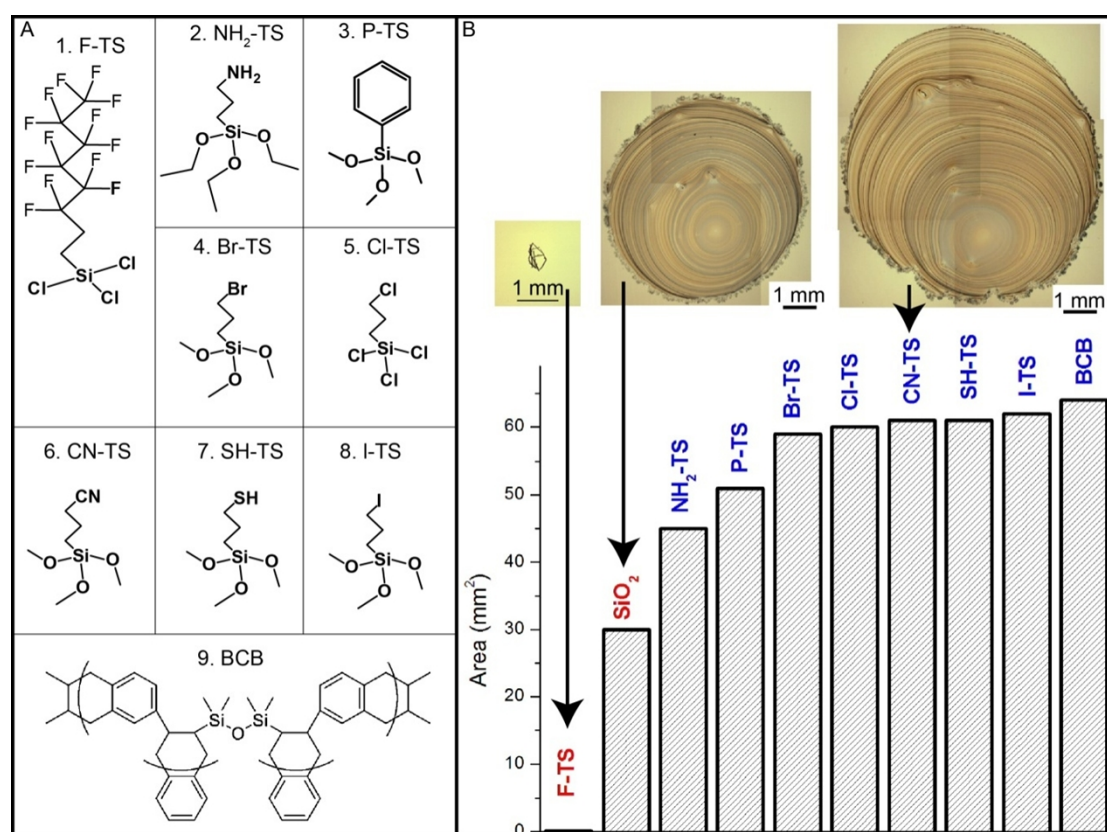
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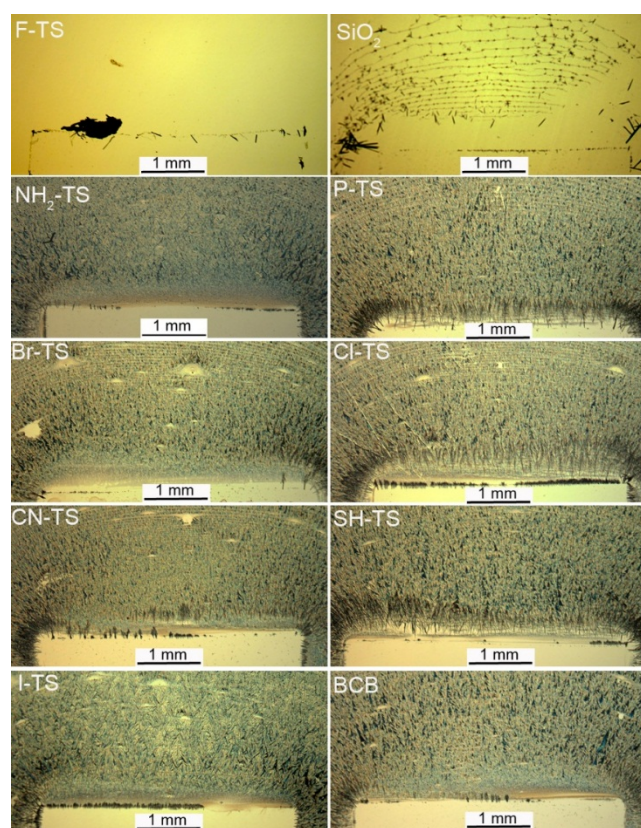
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**Fig. S1** (A) The molecular structures of the chemicals used for surface modification of the wafer.

(B) The wettability of the C<sub>60</sub> solution (0.4 mg/mL in m-xylene) on the surfaces of the modified wafers. The wettability was characterized by the spreading area of a solution droplet (1 μL) on the wafers. The larger the area the droplet spreads onto, the better the wetting is.



**Fig. S2** OM images of crystals grown from  $C_{60}$  solutions (0.4 mg/mL in m-xylene) on varied substrates.